

8961726 TEXAS INSTR (OPTO)

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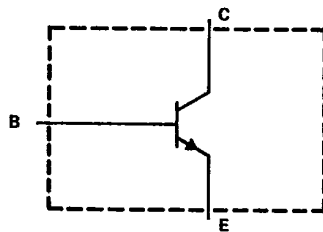
TIPL757, TIPL757A
N-P-N SILICON POWER TRANSISTORS

REVISED OCTOBER 1984

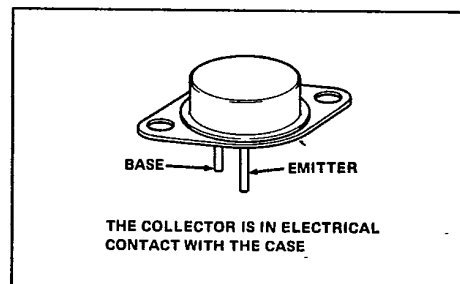
T-33-15

- 200 W at 25° C Case Temperature
- 15 A Continuous Collector Current
- 25 A Peak Collector Current
- Operating Characteristics Fully Guaranteed at 100° C
- Transient Power Dissipation Guaranteed at 100° C
- $I_{CES} < 100 \mu A$ at Maximum Rated V_{CE} at 100° C
- 1000 V Blocking Capability
- $V_{CEO(sus)}$ TIPL757 . . . 375 V Min.
TIPL757A . . . 420 V Min.
- Specifically Designed for High-Voltage, Inductive Load Switching Applications

device schematic



TO-3 PACKAGE



absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	TIPL757	TIPL757A
Collector-base voltage	800 V	1000 V
Collector-emitter voltage ($V_{BE} = 0$)	800 V	1000 V
Collector-emitter voltage ($I_B = 0$)	375 V	420 V
Base-emitter voltage	10 V	
Continuous base current	15 A	
Peak collector current (see Note 1)	25 A	
Continuous device dissipation at (or below) 25°C case temperature (see Figure 14)	200 W	
Operating junction and storage temperature range	- 65°C to 200°C	

NOTE 1: This value applies for $t_W = 2$ ms, duty cycle $\leq 2\%$.

TIPL Devices

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